Unit: mm

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type ($L^2-\pi$ -MOSV)

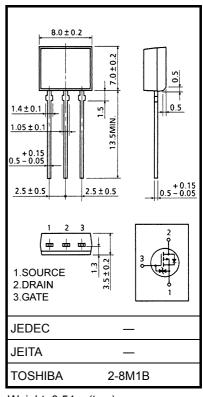
2SJ525

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance $: R_{DS} (ON) = 0.1 \Omega (typ.)$
- High forward transfer admittance $|Y_{fs}| = 4.5 \text{ S (typ.)}$
- Low leakage current $: I_{DSS} = -100 \ \mu A \ (max) \ (V_{DS} = -30 \ V)$
- Enhancement mode $: V_{th} = -0.8 \sim -2.0 \text{ V} (V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	-30	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	-30	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	-5	А	
	Pulse (Note 1)	I _{DP}	-20	А	
Drain power dissipation	n (Ta = 25°C)	PD	1.3	W	
Single pulse avalanche energy (Note 2)		E _{AS}	517	mJ	
Avalanche current		I _{AR}	-5	А	
Repetitive avalanche energy (Note 3)		E _{AR}	0.13	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 0.54 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R _{th (ch−a)}	96.1	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = -25 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 14.84 mH, $R_G = 25 \Omega$, $I_D = -5 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

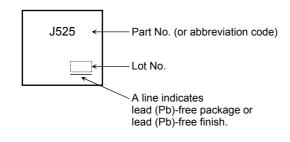
Electrical Characteristics (Ta = 25°C)

Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cu	rrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V		_	±10	μA	
Drain cut-off cu	rrent	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-100	μA	
Drain−source br voltage	eakdown	V (BR) DSS	I _D = -10 mA, V _{GS} = 0 V	-30	_	_	V	
Gate threshold v	voltage	V _{th}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$	-0.8	_	-2.0	V	
Drain-source ON resistance		R _{DS (ON)}	V_{GS} = -4 V, I _D = -2.5 A	—	0.17	0.2	Ω	
			V _{GS} = -10 V, I _D = -2.5 A	_	0.1	0.12	12	
Forward transfer	admittance	Y _{fs}	V _{DS} = -10 V, I _D = -2.5 A	2.0	4.5	_	S	
Input capacitance	e	C _{iss}			850	_	pF	
Reverse transfer capacitance		C _{rss}	V_{DS} = -10 V, V_{GS} = 0 V, f = 1 MHz	_	250	_		
Output capacitance		Coss			330	_		
Switching time	Rise time	tr	$V_{GS} = 10V$ $V_{GS} = 10V$ $V_{DD} = -15V$ $Duty \le 1\%, t_{W} = 10\mu s$	_	50	_		
	Turn-on time	t _{on}		_	75	_	• ns	
	Fall time	t _f			20	_		
	Turn-off time	t _{off}			95	_		
Total gate charge (Gate-source plus gate-drain)		Qg	V _{DD} ≈ −24 V, V _{GS} = −10 V,	_	27	_		
Gate-source charge		Q _{gs}	$I_{\rm D} = -5 \text{ A}$		19	_	nC	
Gate-drain ("miller") charge		Q _{gd}			8	—		

Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	-	_	-5	А
Pulse drain reverse current (Note 1)	I _{DRP}	—	-	-	-20	A
Forward voltage (diode)	V _{DSF}	I _{DR} = -5 A, V _{GS} = 0 V	_	_	1.7	V
Reverse recovery time	t _{rr}	I _{DR} = -5 A, V _{GS} = 0 V	_	60	—	ns
Reverse recovery charge	Q _{rr}	dI _{DR} / dt = 50 A / μs	_	56	_	nC

Marking



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20070701-EN

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